

FEATURES

- 10µs Short Circuit Withstand
- High Thermal Cycling Capability
- Non Punch Through Silicon
- Isolated AISiC Base with AlN Substrates
- Lead Free Construction

APPLICATIONS

- High Reliability Inverters
- Motor Controllers
- Traction Drives

The Powerline range of high power modules includes half bridge, chopper, dual, single and bi-directional switch configurations covering voltages from 600V to 6500V and currents up to 2400A.

The DIM400DCM17-A000 is a 1700V, n-channel enhancement mode, insulated gate bipolar transistor (IGBT) chopper module. The IGBT has a wide reverse bias safe operating area (RBSOA) plus 10µs short circuit withstand. This device is optimised for traction drives and other applications requiring high thermal cycling capability.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

Order As:

DIM400DCM17-A000

Note: When ordering, please use the complete part number

KEY PARAMETERS

V_{CES}	1700V
$V_{CE(sat)}$ * (typ)	2.7V
I_C (max)	400A
$I_{C(PK)}$ (max)	800A

* Measured at the power busbars, not the auxiliary terminals

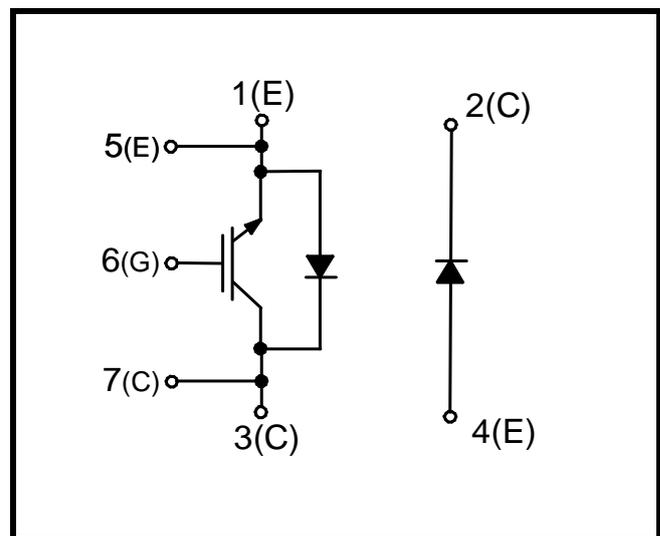
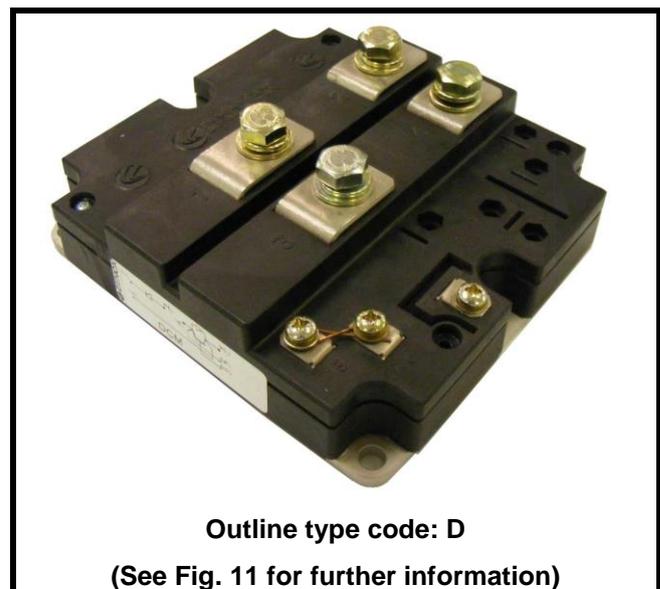


Fig. 1 Circuit configuration



Outline type code: D

(See Fig. 11 for further information)

Fig. 2 Package

ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under ‘Absolute Maximum Ratings’ may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V _{CES}	Collector-emitter voltage	V _{GE} = 0V	1700	V
V _{GES}	Gate-emitter voltage		±20	V
I _C	Continuous collector current	T _{case} = 75°C	400	A
I _{C(PK)}	Peak collector current	1ms, T _{case} = 110°C	800	A
P _{max}	Max. transistor power dissipation	T _{case} = 25°C, T _j = 150°C	3470	W
I ² t	Diode I ² t value (IGBT arm)	V _R = 0, t _p = 10ms, T _j = 125°C	30	kA ² s
	Diode I ² t value (Diode arm)		120	kA ² s
V _{isol}	Isolation voltage – per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	4000	V
Q _{PD}	Partial discharge – per module	IEC1287, V ₁ = 1800V, V ₂ = 1300V, 50Hz RMS	10	pC

THERMAL AND MECHANICAL RATINGS

Internal insulation material: AIN
 Baseplate material: AISiC
 Creepage distance: 20mm
 Clearance: 10mm
 CTI (Comparative Tracking Index): 350

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
R _{th(j-c)}	Thermal resistance – transistor (per arm)	Continuous dissipation – junction to case	-	-	36	°C/kW
R _{th(j-c)}	Thermal resistance – diode (IGBT arm)	Continuous dissipation – junction to case	-	-	80	°C/kW
	Thermal resistance – diode (Diode arm)		-	-	40	°C/kW
R _{th(c-h)}	Thermal resistance – case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	-	8	°C/kW
T _j	Junction temperature	Transistor	-	-	150	°C
		Diode	-	-	125	°C
T _{stg}	Storage temperature range	-	-40	-	125	°C
	Screw torque	Mounting – M6	-	-	5	Nm
		Electrical connections – M4	-	-	2	Nm
		Electrical connections – M8	-	-	10	Nm

ELECTRICAL CHARACTERISTICS

T_{case} = 25°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
I _{CES}	Collector cut-off current	V _{GE} = 0V, V _{CE} = V _{CES}			1	mA
		V _{GE} = 0V, V _{CE} = V _{CES} , T _{case} = 125°C			12	mA
I _{GES}	Gate leakage current	V _{GE} = ± 20V, V _{CE} = 0V			2	µA
V _{GE(TH)}	Gate threshold voltage	I _C = 20mA, V _{GE} = V _{CE}	4.5	5.5	6.5	V
V _{CE(sat)} †	Collector-emitter saturation voltage	V _{GE} = 15V, I _C = 400A		2.7	3.2	V
		V _{GE} = 15V, I _C = 400A, T _j = 125°C		3.4	4.0	V
I _F	Diode forward current	DC			400	A
I _{FM}	Diode maximum forward current	t _p = 1ms			800	A
V _F †	Diode forward voltage (IGBT arm)	I _F = 400A		2.2	2.5	V
	Diode forward voltage (Diode arm)			1.8	2.1	V
	Diode forward voltage (IGBT arm)	I _F = 400A, T _j = 125°C		2.3	2.6	V
	Diode forward voltage (Diode arm)			1.8	2.1	V
C _{ies}	Input capacitance	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz		30		nF
Q _g	Gate charge	±15V		4.5		µC
C _{res}	Reverse transfer capacitance	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz		2.5		nF
L _M	Module inductance – per arm			20		nH
R _{INT}	Internal transistor resistance – per arm			270		µΩ
SC _{Data}	Short circuit current, I _{SC}	T _j = 125°C, V _{CC} = 1000V t _p ≤ 10µs, V _{GE} ≤ 15V V _{CE(max)} = V _{CES} - L* x di/dt IEC 60747-9		1600		A

Note:

† Measured at the power busbars, not the auxiliary terminals

* L is the circuit inductance + L_M

ELECTRICAL CHARACTERISTICS

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units	
t _{d(off)}	Turn-off delay time	I _C = 400A V _{GE} = ±15V V _{CE} = 900V R _{G(ON)} = 4.7Ω R _{G(OFF)} = 4.7Ω L _S ~ 100nH		1150		ns	
t _f	Fall time			100		ns	
E _{OFF}	Turn-off energy loss				120		mJ
t _{d(on)}	Turn-on delay time				250		ns
t _r	Rise time				250		ns
E _{ON}	Turn-on energy loss				150		mJ
Q _{rr}	Diode reverse recovery charge	IGBT arm I _F = 400A V _{CE} = 900V di _F /dt = 2000A/μs		100		μC	
I _{rr}	Diode reverse recovery current				230		A
E _{rec}	Diode reverse recovery energy				70		mJ
Q _{rr}	Diode reverse recovery charge	Diode arm I _F = 400A V _{CE} = 900V di _F /dt = 2000A/μs		130		μC	
I _{rr}	Diode reverse recovery current				300		A
E _{rec}	Diode reverse recovery energy				90		mJ

T_{case} = 125°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units	
t _{d(off)}	Turn-off delay time	I _C = 400A V _{GE} = ±15V V _{CE} = 900V R _{G(ON)} = 4.7Ω R _{G(OFF)} = 4.7Ω L _S ~ 100nH		1400		ns	
t _f	Fall time				130		ns
E _{OFF}	Turn-off energy loss				180		mJ
t _{d(on)}	Turn-on delay time				400		ns
t _r	Rise time				250		ns
E _{ON}	Turn-on energy loss				170		mJ
Q _{rr}	Diode reverse recovery charge	IGBT arm I _F = 400A V _{CE} = 900V di _F /dt = 2000A/μs		170		μC	
I _{rr}	Diode reverse recovery current				270		A
E _{rec}	Diode reverse recovery energy				100		mJ
Q _{rr}	Diode reverse recovery charge	Diode arm I _F = 400A V _{CE} = 900V di _F /dt = 2000A/μs		220		μC	
I _{rr}	Diode reverse recovery current				350		A
E _{rec}	Diode reverse recovery energy				130		mJ

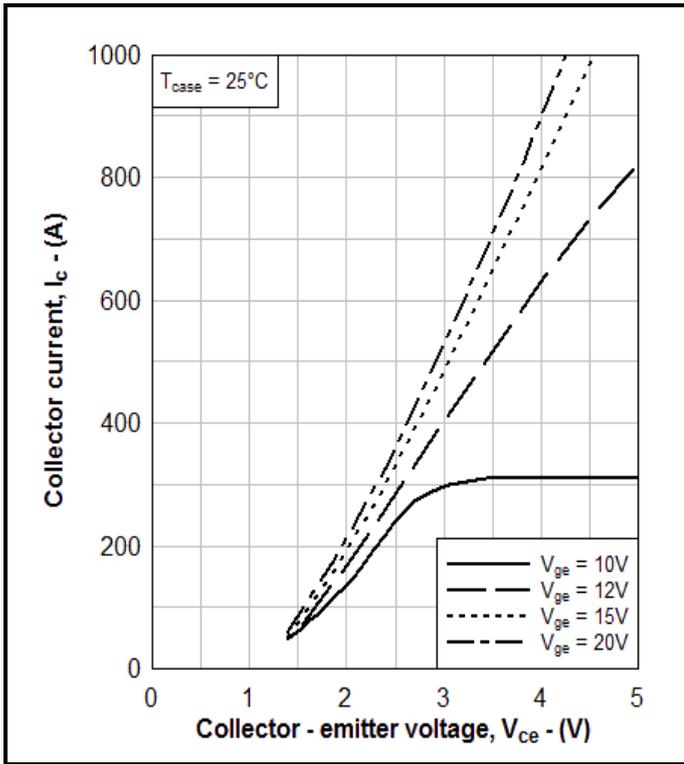


Fig. 3 Typical output characteristics

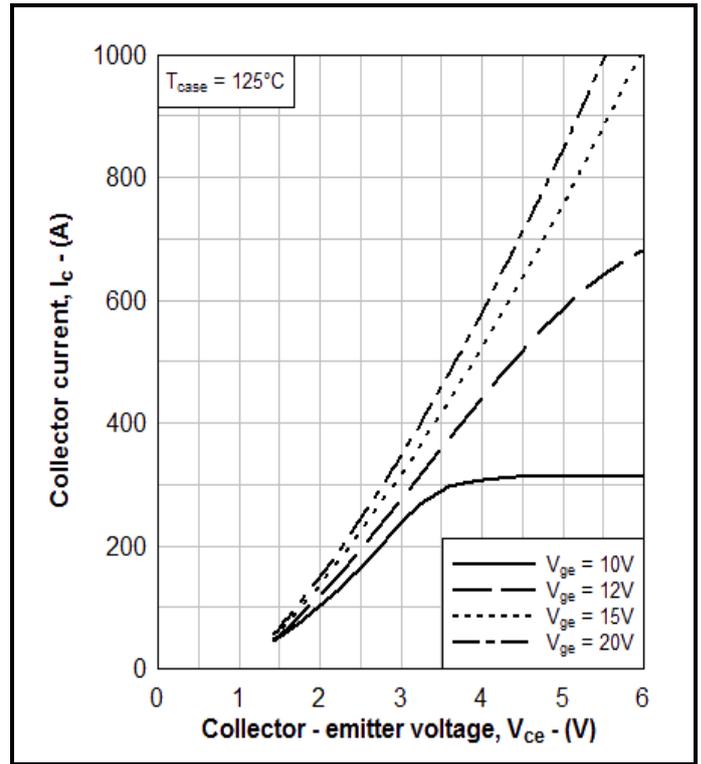


Fig. 4 Typical output characteristics

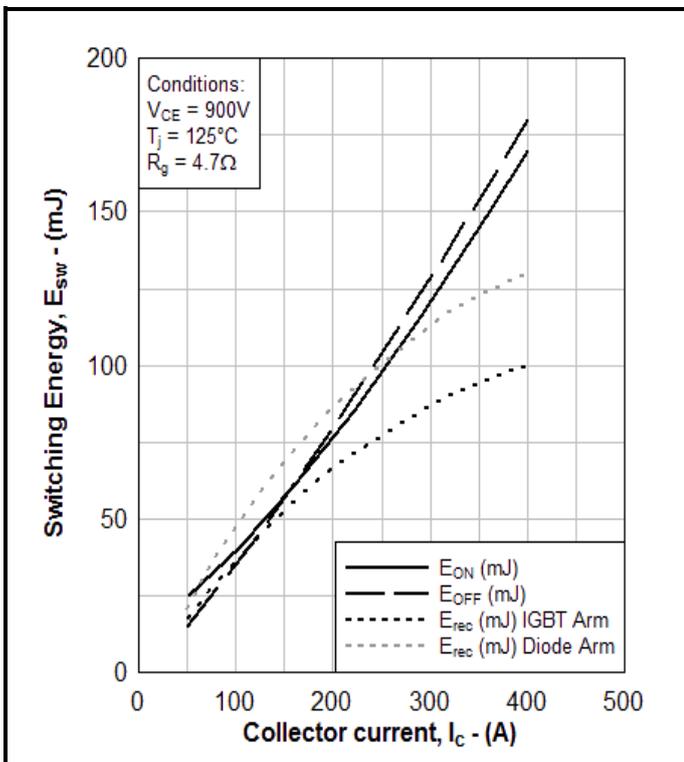


Fig. 5 Typical switching energy vs collector current

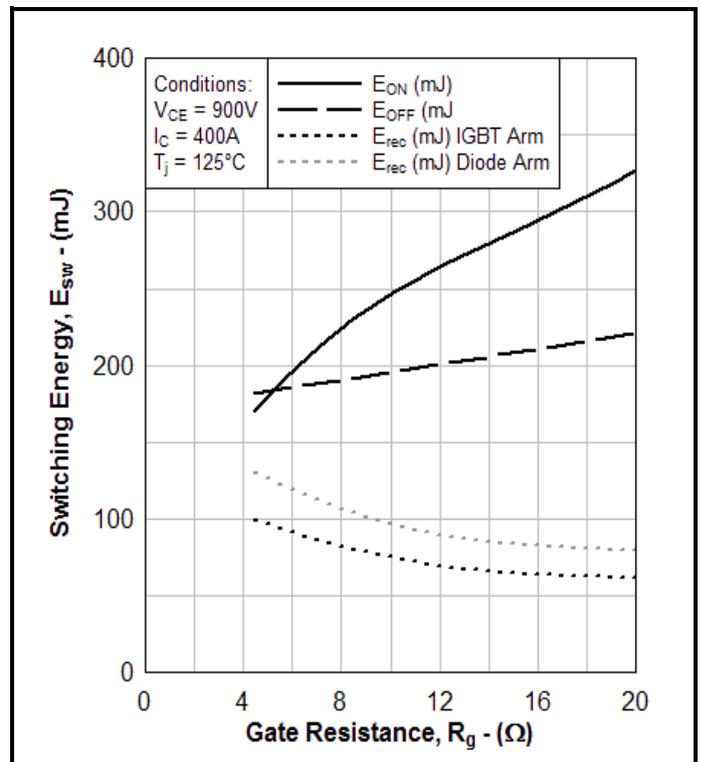


Fig. 6 Typical switching energy vs gate resistance

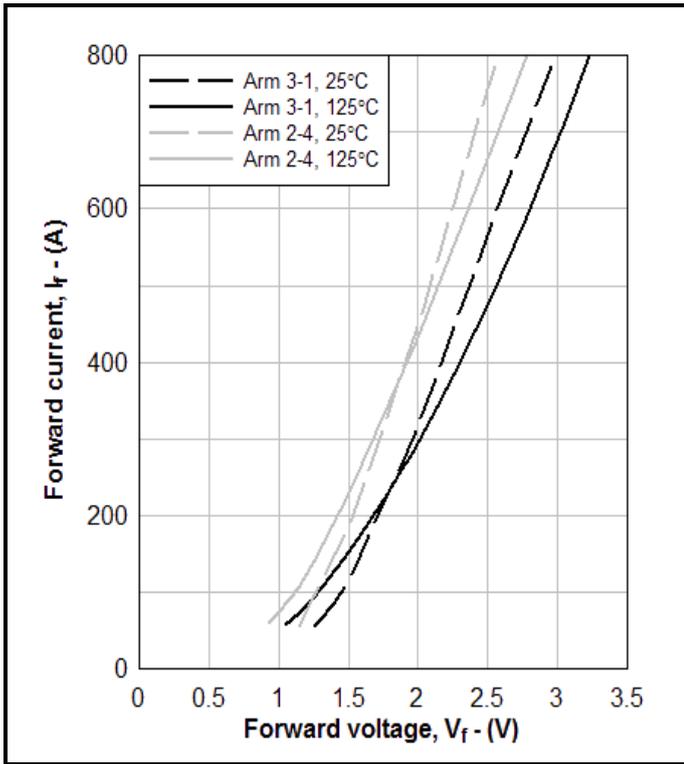


Fig. 7 Diode typical forward characteristics

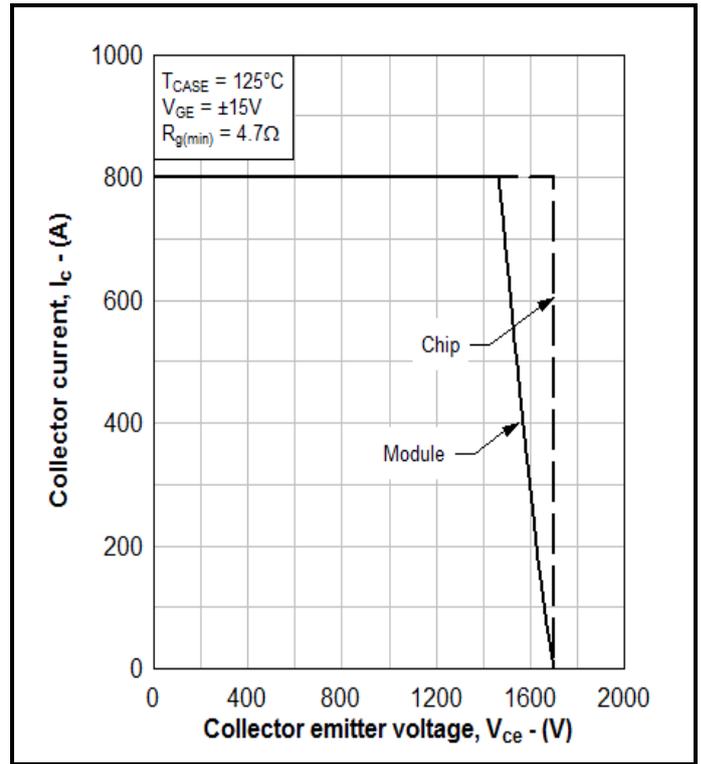


Fig. 8 Reverse bias safe operating area

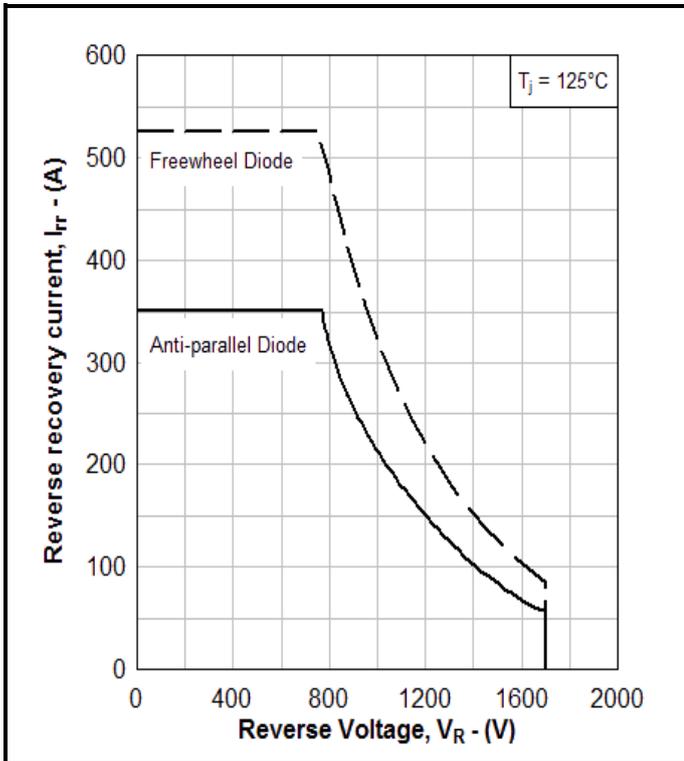


Fig. 9 Diode reverse bias safe operating area

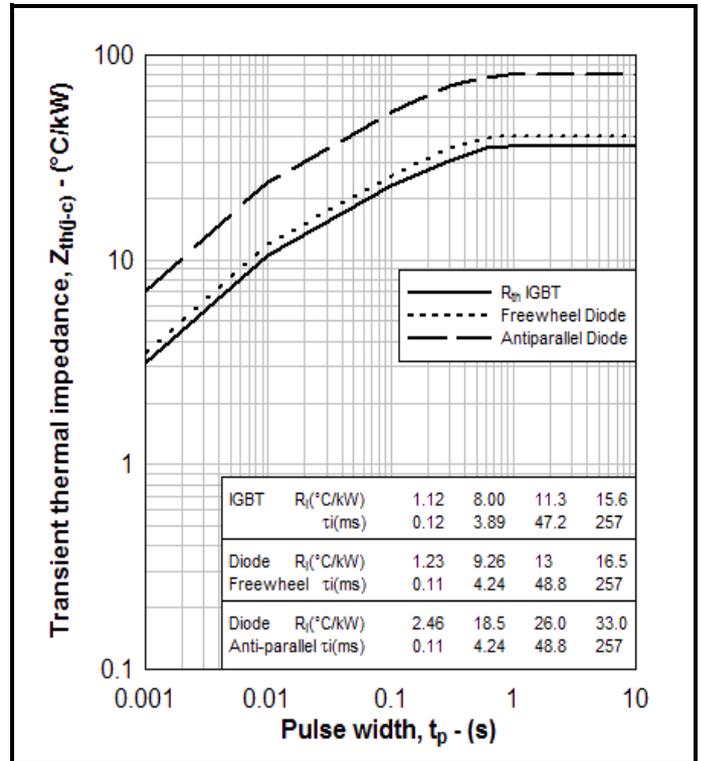
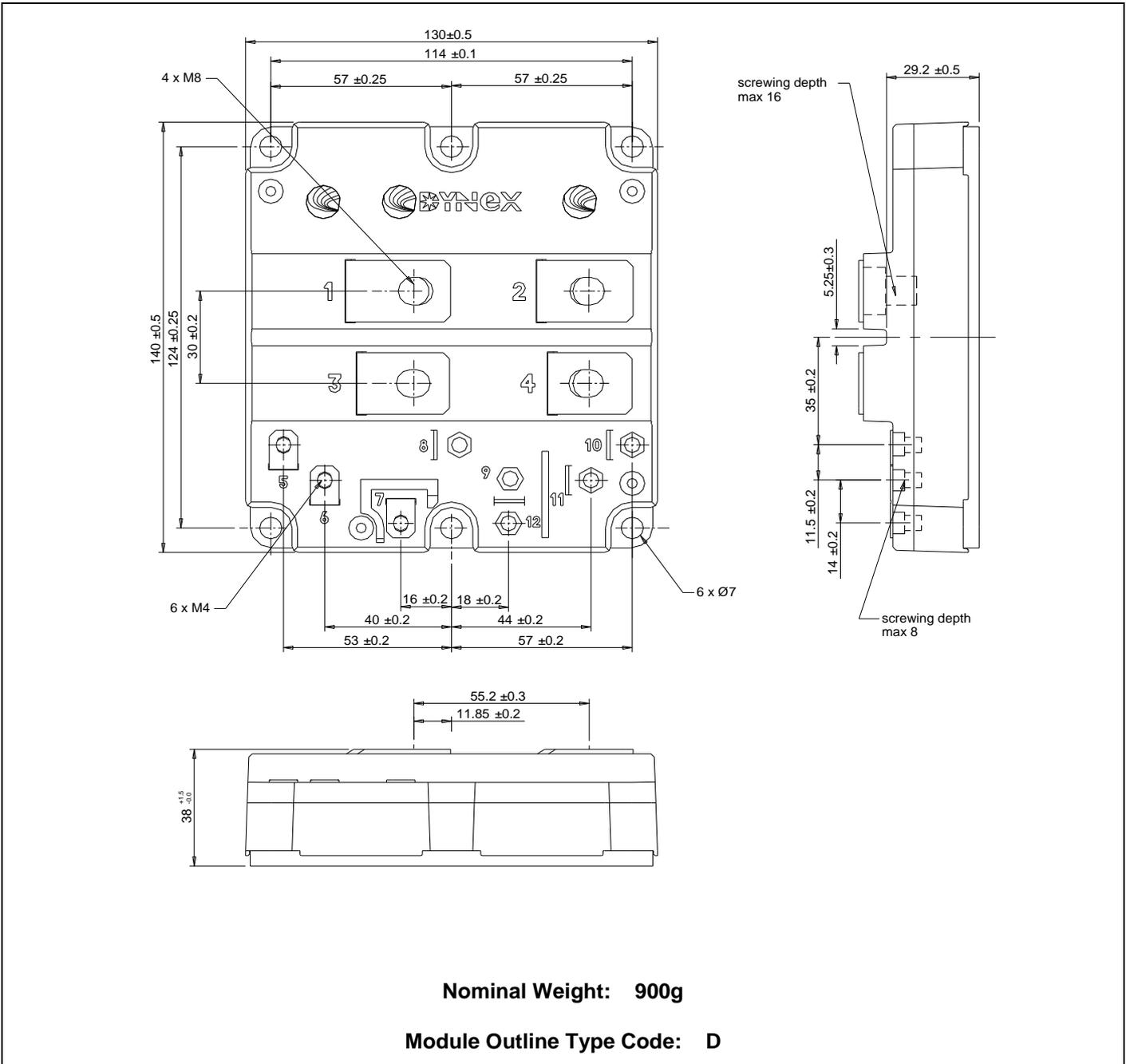


Fig. 10 Transient thermal impedance

PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services.
 All dimensions in mm, unless stated otherwise.
DO NOT SCALE.



Nominal Weight: 900g

Module Outline Type Code: D

Fig. 11 Module outline drawing

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